INFORMATION DISCLOSURE

STATEMENT

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U.S. PATENT AND TRADEMARK OFFICE

October 13, 2005

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Group Art Unit: tba Examiner: tba

In Re	PATENT	APPI	ICATION	OF

Applicant(s): Alexandre ELLISON et al.

Appl. No.: 10/526,259

Filing Date: February 28, 2005

rining Date. rebitary 28, 2003

For: LIGHTLY DOPED SILICON CARBIDE WAFER AND USE THEREOF IN HIGH POWER DEVICES

Atty. Dkt.: 35947-213490

Commissioner for Patents P.O. Box 1450

Alexandria, VA 22313-1450

Sir:

This is an Information Disclosure Statement submitted under 37 C.F.R. § 1.97 within the time specified under 37 C.F.R. § 1.97(b).

Enclosed is a PTO-1449, and copies of references cited therein.

This Information Disclosure Statement is being filed before the mailing date of a first Office Action on the merits.

Date: ___(D/(3/05_

Respectfully submitted,

Eric J. Franklin, Registration No. 37.134

VENABLE

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Approved for up th 10/31/2002. OMB 0851-0031

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Examiner Signature	/Nicole T. Gugliotta/	Date Considered	10/24/2007	

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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